

Please **replace** the pending abstract with the following abstract of the disclosure:

#### ABSTRACT

A III nitride single-crystal manufacturing method in which a liquid layer (3) of 200  $\mu\text{m}$  or less thickness is formed in between a substrate (1) and a III nitride source-material baseplate (2), and III nitride single crystal (4) is grown onto the face (1s) on the liquid-layer side of the substrate (1). Herein, the substrate (1) in at least a superficial layer (1a) on the liquid-layer side may be formed of a III nitride single crystal, while the III nitride source-material baseplate (2) can be formed of a III nitride polycrystal. Further, the substrate (1) in at least a superficial layer (1a) on the liquid-layer side, and the III nitride source-material baseplate (2) can be formed of a III nitride single crystal, while the face (1s) on the liquid-layer side of the substrate (1) can be made a III-atom surface, and the face (2s) on the liquid-layer side of the III nitride source-material baseplate (2) can be made a nitrogen-atom surface.